

Cambridge University Press

978-1-107-40798-5 - Materials and Devices for End-of-Roadmap and Beyond CMOS

Scaling: Materials Research Society Symposium Proceedings: Volume 1252

Editors: Shriram Ramanathan, Supratik Guha, Jochen Mannhart, Andrew C. Kummel,

Heiji Watanabe, Iain Thayne and Prashant Majhi

Frontmatter

[More information](#)

Materials and Devices for End-of-Roadmap and Beyond CMOS Scaling

Cambridge University Press

978-1-107-40798-5 - Materials and Devices for End-of-Roadmap and Beyond CMOS

Scaling: Materials Research Society Symposium Proceedings: Volume 1252

Editors: Shriram Ramanathan, Supratik Guha, Jochen Mannhart, Andrew C. Kummel,

Heiji Watanabe, Iain Thayne and Prashant Majhi

Frontmatter

[More information](#)

Cambridge University Press

978-1-107-40798-5 - Materials and Devices for End-of-Roadmap and Beyond CMOS Scaling: Materials Research Society Symposium Proceedings: Volume 1252
Editors: Shriram Ramanathan, Supratik Guha, Jochen Mannhart, Andrew C. Kummel, Heiji Watanabe, Iain Thayne and Prashant Majhi

Frontmatter

[More information](#)

**MATERIALS RESEARCH SOCIETY
SYMPOSIUM PROCEEDINGS VOLUME 1252**

**Materials and Devices
for End-of-Roadmap
and Beyond CMOS Scaling**

Symposium held April 5–9, 2010, San Francisco, California

EDITORS:

Shriram Ramanathan

Harvard University
Cambridge, Massachusetts, U.S.A.

Andrew C. Kummel

University of California—San Diego
San Diego, California, U.S.A.

Supratik Guha

IBM Thomas J. Watson Research Center
Yorktown Heights, New York, U.S.A.

Heiji Watanabe

Osaka University
Osaka, Japan

Jochen Mannhart

Center for Electronic Correlations and
Magnetism
Institute of Physics
University of Augsburg
Augsburg, Germany

Iain Thayne

University of Glasgow
Glasgow, Scotland, U.K.

Prashant Majhi

Sematech/Intel
Austin, Texas, U.S.A.



Materials Research Society
Warrendale, Pennsylvania

Cambridge University Press

978-1-107-40798-5 - Materials and Devices for End-of-Roadmap and Beyond CMOS

Scaling: Materials Research Society Symposium Proceedings: Volume 1252

Editors: Shriram Ramanathan, Supratik Guha, Jochen Mannhart, Andrew C. Kummel,

Heiji Watanabe, Iain Thayne and Prashant Majhi

Frontmatter

[More information](#)

CAMBRIDGE UNIVERSITY PRESS

Cambridge, New York, Melbourne, Madrid, Cape Town,

Singapore, São Paulo, Delhi, Mexico City

Cambridge University Press

32 Avenue of the Americas, New York NY 10013-2473, USA

Published in the United States of America by Cambridge University Press, New York

www.cambridge.org

Information on this title: www.cambridge.org/9781107407985

Materials Research Society

506 Keystone Drive, Warrendale, PA 15086

<http://www.mrs.org>

© Materials Research Society 2010

This publication is in copyright. Subject to statutory exception
and to the provisions of relevant collective licensing agreements,
no reproduction of any part may take place without the written
permission of Cambridge University Press.

This publication has been registered with Copyright Clearance Center, Inc.
For further information please contact the Copyright Clearance Center,

Salem, Massachusetts.

First published 2010

First paperback edition 2012

Single article reprints from this publication are available through
University Microfilms Inc., 300 North Zeeb Road, Ann Arbor, MI 48106

CODEN: MRSPDH

ISBN 978-1-107-40798-5 Paperback

Cambridge University Press has no responsibility for the persistence or
accuracy of URLs for external or third-party internet websites referred to in
this publication, and does not guarantee that any content on such websites is,
or will remain, accurate or appropriate.

Cambridge University Press

978-1-107-40798-5 - Materials and Devices for End-of-Roadmap and Beyond CMOS
 Scaling: Materials Research Society Symposium Proceedings: Volume 1252
 Editors: Shriram Ramanathan, Supratik Guha, Jochen Mannhart, Andrew C. Kummel,
 Heiji Watanabe, Iain Thayne and Prashant Majhi
 Frontmatter

[More information](#)

CONTENTS

Preface	ix
----------------------	----

Materials Research Society Symposium Proceedings.....	x
--	---

NOVEL DEVICES

* Tunneling MOSFETs Based on III-V Staggered Heterojunctions	3
---	---

P.M. Asbeck, L. Wang, S. Gu, Y. Taur, and E.T. Yu

Tunable CMOS and Current Mirror Circuit with Double-Gate Screen Grid Field Effect Transistors.....	11
---	----

Y. Shadrokh, K. Fobelets, and J.E. Velazquez-Perez

A New SiGeC Vertical MOSFET: Single-Device CMOS (SD-CMOS)	17
--	----

Carlos J.R.P. Augusto and Lynn Forester

Ge MOSFET

Epitaxial Dy₂O₃ Thin Films Grown on Ge(100) Substrates by Molecular Beam Epitaxy	27
---	----

Md. Nurul Kabir Bhuiyan, Mariela Menghini,
 Christel Dieker, Jin Won Seo, Jean-Pierre Locquet,
 Roumen Vitchev, and Chiara Marchiori

Investigation of the Thermal Stability of Strained Ge Layers Grown at Low Temperature by Reduced-Pressure Chemical Vapour Deposition on Relaxed Si_{0.2}Ge_{0.8} Buffers	35
---	----

A. Dobbie, M. Myronov, Xue-Chao Liu,
 Van H. Nguyen, E.H.C. Parker, and D.R. Leadley

High Electron Mobility in Ge nMISFETs With High Quality S/D Formed by Solid Source Diffusions.....	41
---	----

Tatsuro Maeda, Yukinori Morita,
 and Shinichi Takagi

*Invited Paper

Cambridge University Press

978-1-107-40798-5 - Materials and Devices for End-of-Roadmap and Beyond CMOS Scaling: Materials Research Society Symposium Proceedings: Volume 1252
 Editors: Shriram Ramanathan, Supratik Guha, Jochen Mannhart, Andrew C. Kummel, Heiji Watanabe, Iain Thayne and Prashant Majhi
 Frontmatter

[More information](#)***POSTER SESSION***

Investigation of Wet Etch of Sub-nm LaO_x Capping Layers for CMOS Applications	49
Hui-Feng Li, Mo Jahanbani, Martin Rodgers, Steve Bennett, Daniel Franca, Corbet Johnson, Steven Gausepohl, and Joseph Piccirillo, Jr.	
Profiling Different Kinds of Generated Defects at Elevated Temperature in Both SiO₂ and High-k Dielectrics	55
S. Sahhaf, R. Degraeve, M.B. Zahid, and G. Groeseneken	
Electrical Characteristics of Crystalline Gd₂O₃ Film on Si (111): Impacts of Growth Temperature and Post Deposition Annealing	61
G. Niu, B. Vilquin, N. Baboux, G. Saint-Girons, C. Plossu, and G. Hollinger	
Nanoscale Study of the Influence of Atomic Oxygen on the Electrical Properties of LaAlO₃ Thin High-k Oxide Films Deposited by Molecular Beam Epitaxy	67
Wael Hourani, Liviu Militaru, Brice Gautier, David Albertini, Armel Descamps-Mandine, Sylvain Pelloquin, Carole Plossu, and Guillaume Saint-Girons	
Impact of Ge Doping on Si Substrate and Diode Characteristics	73
J. Vanhellemont, J. Lauwaert, J. Chen, H. Vrielinck, J.M. Raffi, H. Ohyama, E. Simoen, and D. Yang	
Contact Technology Using Pulsed Laser Annealing to Form Ti/Al Ohmic Contacts on n-type GaN with Lower Contact Resistance and Improved Surface Morphology	79
Grace Huiqi Wang, Xincai Wang, Debbie Hwee Leng Seng, Hongyu Zheng, Yong Lim Foo, and Sudhiranjan Tripathy	
Micro Probe Carrier Profiling of Ultra-Shallow Structures in Germanium	87
Trudo Clarysse, Alain Moussa, Brigitte Parmentier, Pierre Eyben, Bastien Douhard, Wilfried Vandervorst, Peter F. Nielsen, Rong Lin, Dirch H. Petersen, Fei Wang, and Ole Hansen	

Cambridge University Press

978-1-107-40798-5 - Materials and Devices for End-of-Roadmap and Beyond CMOS Scaling: Materials Research Society Symposium Proceedings: Volume 1252
 Editors: Shriram Ramanathan, Supratik Guha, Jochen Mannhart, Andrew C. Kummel, Heiji Watanabe, Iain Thayne and Prashant Majhi
 Frontmatter

[More information](#)***III-V MOSFET***

Band Offset Control by Interfacial Oxygen Content at GaAs:HfO₂ Interfaces	95
Weichao Wang, Robert M. Wallace, and Kyeongjae Cho	
Origins for Electron Mobility Improvement in InGaAs MISFETs with (NH₄)₂S Treatment	105
Y. Urabe, N. Miyata, T. Yasuda, H. Ishii, T. Itatani, H. Yamada, N. Fukuhara, M. Hata, M. Yokoyama, M. Takenaka, and S. Takagi	

NOVEL DEVICES AND III-V MOSFET

Study of Germanium Epitaxial Recrystallization on Bulk-Si Substrates	113
Byron Ho, Reinaldo Vega, and Tsu-Jae King-Liu	
Interfacial Properties, Surface Morphology and Thermal Stability of Epitaxial GaAs on Ge Substrates with High-k Dielectric for Advanced CMOS Applications	119
A. Kumar, G.K. Dalapati, Terence Kin Shun Wong, M.K. Kumar, C.K. Chia, H. Gao, B.Z. Wang, A.S. Wong, and D.Z. Chi	
Interface Study of SiO₂/HfO₂/SiO₂ Stacks Used as InterPoly Dielectric for Future Generations of Embedded Flash Memories	125
A. Guiraud, N. Breil, M. Gros-Jean, D. Deleruyelle, G. Micolau, C. Muller, N. Chérault, and P. Morin	

MATERIALS AND DEVICES FOR BEYOND CMOS SCALING

Fabrication and Current-Voltage Characteristics of Ni Spin Quantum Cross Devices with P3HT:PCBM Organic Materials	133
Hideo Kaiju, Kenji Kondo, Nubla Basheer, Nobuyoshi Kawaguchi, Susanne White, Akihiko Hirata, Manabu Ishimaru, Yoshihiko Hirotsu, and Akira Ishibashi	

Cambridge University Press

978-1-107-40798-5 - Materials and Devices for End-of-Roadmap and Beyond CMOS
Scaling: Materials Research Society Symposium Proceedings: Volume 1252
Editors: Shriram Ramanathan, Supratik Guha, Jochen Mannhart, Andrew C. Kummel,
Heiji Watanabe, Iain Thayne and Prashant Majhi

Frontmatter

[More information](#)

Optically Active Defects in an InAsP/InP Quantum Well Monolithically Integrated on SrTiO₃ (001)	139
J. Cheng, A. El Akra, C. Bru-Chevallier, G. Patriarche, L. Largeau, P. Regreny, G. Hollinger, and G. Saint-Girons	
Author Index	147
Subject Index	149

Cambridge University Press

978-1-107-40798-5 - Materials and Devices for End-of-Roadmap and Beyond CMOS Scaling: Materials Research Society Symposium Proceedings: Volume 1252
Editors: Shriram Ramanathan, Supratik Guha, Jochen Mannhart, Andrew C. Kummel, Heiji Watanabe, Iain Thayne and Prashant Majhi
Frontmatter

[More information](#)

PREFACE

This proceedings volume contains papers presented at Symposium I, "Materials for End-of-Roadmap Scaling of CMOS Devices," and Symposium J, "Materials and Devices for Beyond CMOS Scaling," held April 5–9 at the 2010 MRS Spring Meeting in San Francisco, California. These symposia attracted 106 presentations, of which 22 were invited.

Historically, scaling in Si CMOS was primarily led by lithography. In the last decade, this situation has been completely revolutionized with the introduction of the likes of copper interconnects, high-k gate dielectrics, metal gates, and strained silicon to meet the demands of the International Technology Roadmap for Semiconductors as the technology generations were reduced beyond 45 nm. As we look towards the end of the roadmap and beyond, the proliferation of potential solutions to meet the necessary performance challenges becomes truly staggering, and has motivated an exponential increase in research in a wide range of emerging materials and devices architectures.

This volume contains the refereed versions of numerous papers presented in the symposia which collectively capture the diversity of research activity being actively pursued around the world to address the very significant challenges faced at the end of the CMOS Roadmap and beyond. We believe the papers in this volume are a very revealing "snapshot in time" of the state of research in this dynamic field, and that this collection will be of significant benefit to researchers in the area, both now and in future, as a valuable reference.

The organizers are indebted to the speakers for their interest and support of the symposia by submitting such high quality abstracts and excellent, captivating presentations and posters.

We are very grateful to the staff of the Materials Research Society, who was of enormous assistance at all stages before, during, and after the symposia and during the publication period.

Andrew Kummel
Heiji Watanabe
Iain Thayne
Prashant Majhi
Supratik Guha
Jochen Mannhart
Shriram Ramanathan

November 2010

Cambridge University Press

978-1-107-40798-5 - Materials and Devices for End-of-Roadmap and Beyond CMOS

Scaling: Materials Research Society Symposium Proceedings: Volume 1252

Editors: Shriram Ramanathan, Supratik Guha, Jochen Mannhart, Andrew C. Kummel, Heiji Watanabe, Iain Thayne and Prashant Majhi

Frontmatter

[More information](#)

MATERIALS RESEARCH SOCIETY SYMPOSIUM PROCEEDINGS

- Volume 1245** — Amorphous and Polycrystalline Thin-Film Silicon Science and Technology—2010, Q. Wang, B. Yan, C.C. Tsai, S. Higashi, A. Flewitt, 2010, ISBN 978-1-60511-222-0
- Volume 1246** — Silicon Carbide 2010—Materials, Processing and Devices, S.E. Saddow, E.K. Sanchez, F. Zhao, M. Dudley, 2010, ISBN 978-1-60511-223-7
- Volume 1247E** — Solution Processing of Inorganic and Hybrid Materials for Electronics and Photonics, 2010, ISBN 978-1-60511-224-4
- Volume 1248E** — Plasmonic Materials and Metamaterials, J.A. Dionne, L.A. Sweatlock, G. Shvets, L.P. Lee, 2010, ISBN 978-1-60511-225-1
- Volume 1249** — Advanced Interconnects and Chemical Mechanical Planarization for Micro- and Nanoelectronics, J.W. Bartha, C.L. Borst, D. DeNardis, H. Kim, A. Naeemi, A. Nelson, S.S. Papa Rao, H.W. Ro, D. Toma, 2010, ISBN 978-1-60511-226-8
- Volume 1250** — Materials and Physics for Nonvolatile Memories II, C. Bonafo, Y. Fujisaki, P. Dimitrakos, E. Tokumitsu, 2010, ISBN 978-1-60511-227-5
- Volume 1251E** — Phase-Change Materials for Memory and Reconfigurable Electronics Applications, P. Fons, K. Campbell, B. Cheong, S. Raoux, M. Wuttig, 2010, ISBN 978-1-60511-228-2
- Volume 1252** — Materials and Devices for End-of-Roadmap and Beyond CMOS Scaling, A.C. Kummel, P. Majhi, I. Thayne, H. Watanabe, S. Ramanathan, S. Guha, J. Mannhart, 2010, ISBN 978-1-60511-229-9
- Volume 1253** — Functional Materials and Nanostructures for Chemical and Biochemical Sensing, E. Comini, P. Gouma, G. Malliaras, L. Torsi, 2010, ISBN 978-1-60511-230-5
- Volume 1254E** — Recent Advances and New Discoveries in High-Temperature Superconductivity, S.H. Wee, V. Selvamanickam, Q. Jia, H. Hosono, H.-H. Wen, 2010, ISBN 978-1-60511-231-2
- Volume 1255E** — Structure-Function Relations at Perovskite Surfaces and Interfaces, A.P. Baddorf, U. Diebold, D. Hesse, A. Rappe, N. Shibata, 2010, ISBN 978-1-60511-232-9
- Volume 1256E** — Functional Oxide Nanostructures and Heterostructures, 2010, ISBN 978-1-60511-233-6
- Volume 1257** — Multifunctional Nanoparticle Systems—Coupled Behavior and Applications, Y. Bao, A.M. Dattelbaum, J.B. Tracy, Y. Yin, 2010, ISBN 978-1-60511-234-3
- Volume 1258** — Low-Dimensional Functional Nanostructures—Fabrication, Characterization and Applications, H. Riel, W. Lee, M. Zacharias, M. McAlpine, T. Mayer, H. Fan, M. Knez, S. Wong, 2010, ISBN 978-1-60511-235-0
- Volume 1259E** — Graphene Materials and Devices, M. Chhowalla, 2010, ISBN 978-1-60511-236-7
- Volume 1260** — Photovoltaics and Optoelectronics from Nanoparticles, M. Winterer, W.L. Gladfelter, D.R. Gamelin, S. Oda, 2010, ISBN 978-1-60511-237-4
- Volume 1261E** — Scanning Probe Microscopy—Frontiers in NanoBio Science, C. Durkan, 2010, ISBN 978-1-60511-238-1
- Volume 1262** — *In-Situ* and Operando Probing of Energy Materials at Multiscale Down to Single Atomic Column—The Power of X-Rays, Neutrons and Electron Microscopy, C.M. Wang, N. de Jonge, R.E. Dunin-Borkowski, A. Braun, J-H. Guo, H. Schober, R.E. Winans, 2010, ISBN 978-1-60511-239-8
- Volume 1263E** — Computational Approaches to Materials for Energy, K. Kim, M. van Shilfgaarde, V. Ozolins, G. Ceder, V. Tomar, 2010, ISBN 978-1-60511-240-4
- Volume 1264** — Basic Actinide Science and Materials for Nuclear Applications, J.K. Gibson, S.K. McCall, E.D. Bauer, L. Soderholm, T. Fanghaenel, R. Devanathan, A. Misra, C. Trautmann, B.D. Wirth, 2010, ISBN 978-1-60511-241-1
- Volume 1265** — Scientific Basis for Nuclear Waste Management XXXIV, K.L. Smith, S. Kroeker, B. Uberuaga, K.R. Whittle, 2010, ISBN 978-1-60511-242-8
- Volume 1266E** — Solid-State Batteries, S-H. Lee, A. Hayashi, N. Dudney, K. Takada, 2010, ISBN 978-1-60511-243-5
- Volume 1267** — Thermoelectric Materials 2010—Growth, Properties, Novel Characterization Methods and Applications, H.L. Tuller, J.D. Baniecki, G.J. Snyder, J.A. Malen, 2010, ISBN 978-1-60511-244-2
- Volume 1268** — Defects in Inorganic Photovoltaic Materials, D. Friedman, M. Stavola, W. Walukiewicz, S. Zhang, 2010, ISBN 978-1-60511-245-9
- Volume 1269E** — Polymer Materials and Membranes for Energy Devices, A.M. Herring, J.B. Kerr, S.J. Hamrock, T.A. Zawodzinski, 2010, ISBN 978-1-60511-246-6

Cambridge University Press

978-1-107-40798-5 - Materials and Devices for End-of-Roadmap and Beyond CMOS Scaling: Materials Research Society Symposium Proceedings: Volume 1252
Editors: Shriram Ramanathan, Supratik Guha, Jochen Mannhart, Andrew C. Kummel, Heiji Watanabe, Iain Thayne and Prashant Majhi
Frontmatter

[More information](#)

MATERIALS RESEARCH SOCIETY SYMPOSIUM PROCEEDINGS

- Volume 1270 — Organic Photovoltaics and Related Electronics—From Excitons to Devices,
V.R. Bommisetty, N.S. Sariciftci, K. Narayan, G. Rumbles, P. Peumans, J. van de Lagemaat, G. Dennler, S.E. Shaheen, 2010, ISBN 978-1-60511-247-3
- Volume 1271E —Stretchable Electronics and Conformal Biointerfaces, S.P. Lacour, S. Bauer, J. Rogers, B. Morrison, 2010, ISBN 978-1-60511-248-0
- Volume 1272 — Integrated Miniaturized Materials—From Self-Assembly to Device Integration, C.J. Martinez, J. Cabral, A. Fernandez-Nieves, S. Grego, A. Goyal, Q. Lin, J.J. Urban, J.J. Watkins, A. Saiani, R. Callens, J.H. Collier, A. Donald, W. Murphy, D.H. Gracias, B.A. Grzybowski, P.W.K. Rothemund, O.G. Schmidt, R.R. Naik, P.B. Messersmith, M.M. Stevens, R.V. Ulijn, 2010, ISBN 978-1-60511-249-7
- Volume 1273E —Evaporative Self Assembly of Polymers, Nanoparticles and DNA , B.A. Korgel, 2010, ISBN 978-1-60511-250-3
- Volume 1274 — Biological Materials and Structures in Physiologically Extreme Conditions and Disease, M.J. Buehler, D. Kaplan, C.T. Lim, J. Spatz, 2010, ISBN 978-1-60511-251-0

Prior Materials Research Society Symposium Proceedings available by contacting Materials Research Society